Announcements – Problem Sets

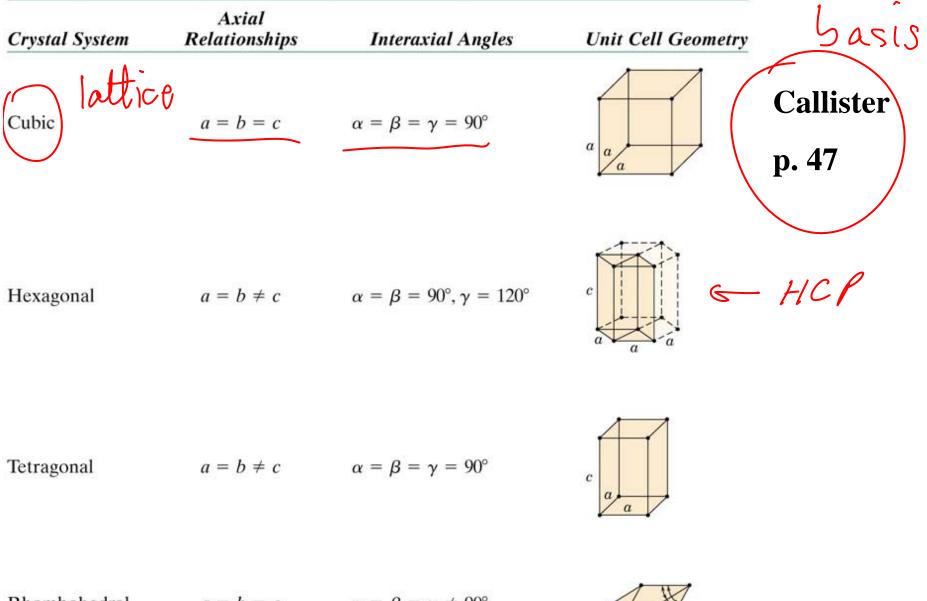
- Set 1 (Assigned 08Jan in lecture): 2.5, 2.6, 2.7, 2.9, 2.11, 2.13, 2.15, 2.18, 2.20, 2.21, 2.22, 3.1, 3.2, 3.5, 3.6, 3.7, 3.10 *SOLUTIONS ON WEBCT NOW*
- Set 2 (Assigned 12Jan via WebCT): 3.17, 3.20, 3.21, 3.37, 3.39, 3.40, 3.41, 3.42, 3.56, 3.57, 3.59
- Problems from Ch. 3 (Sets 1&2) will be addressed in tutorials starting Wednesday.
- Tutorial quizzes begin this Wednesday.

Last time...

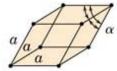
• Close packing (FCC and HCP) for pure metals, also a common non-close packed structure (BCC)

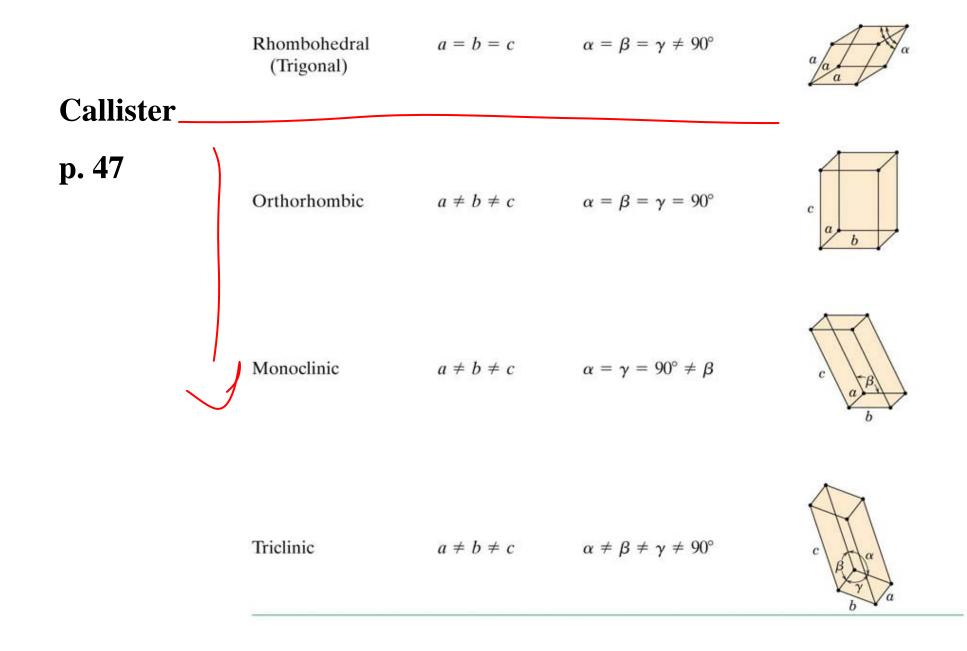
This time...

- More on why it is important
- Points, directions, planes
- Diffraction



Rhombohedral (Trigonal) a = b = c $\alpha = \beta = \gamma \neq 90^{\circ}$





Characterization of Crystal Structure

- Primary tools
 - X-ray diffraction
 - Electron diffraction (in transmission electron microscope)
- Auxiliary tools (to confirm elements present)
 - Scanning electron microscopy + a spectroscopy technique
 - Raman spectroscopy
 - Many others *

Growth of nanowire superlattice structures for nanoscale photonics and electronics

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The assembly of semiconductor nanowires and carbon nanotubes into nanoscale devices and circuits could enable diverse applications in nanoelectronics and photonics1. Individual semiconducting nanowires have already been configured as field-effect transistors², photodetectors³ and bio/chemical sensors⁴. More sophisticated light-ensitting diodes5 (LEDs) and complementary and diode logic6-8 devices have been realized using both n- and ptype semiconducting nanowires or nanotubes. The n- and p-type materials have been incorporated in these latter devices either by crossing p- and n-type nanowires^{2,5,6,9} or by lithographically defining distinct p- and n-type regions in nanotubes^{8,10}, although both strategies limit device complexity. In the planar semiconductor industry, intricate n- and p-type and more generally compositionally modulated (that is, superlattice) structures are used to enable versatile electronic and photonic functions. Here we demonstrate the synthesis of semiconductor nanowire superlattices from group III-V and group IV materials. (The superlattices are created within the nanowires by repeated modulation of the vapour-phase semiconductor reactants during growth of the wires.) Compositionally modulated superlattices consisting of 2 to 21 layers of GaAs and GaP have been prepared. Furthermore, n-Si/p-Si and n InF/p-InF modulation doped nanowires have been synthesized. Single-nanowire photoluminescence, electrical transport and electroluminescence measurements show the unique Photonic and electronic properties of these nanowire superlattices, and suggest potential applications ranging from nano-barcodes to polarized nanoscale LEDs.

'Cutting edge' electrical engineering example

Linked to on WebCT:

M.S. Gudiksen, et al. Nature 415, 617 (2002).

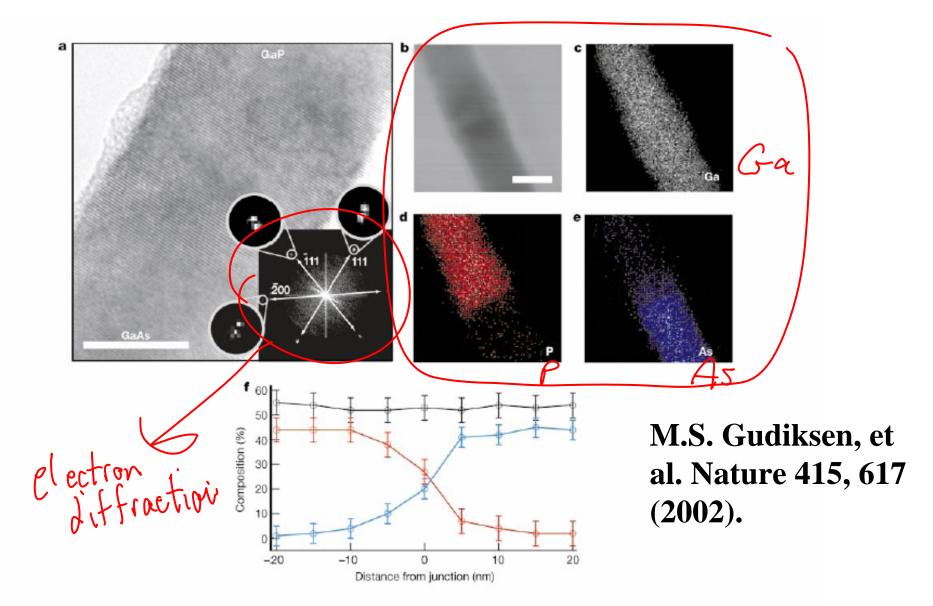
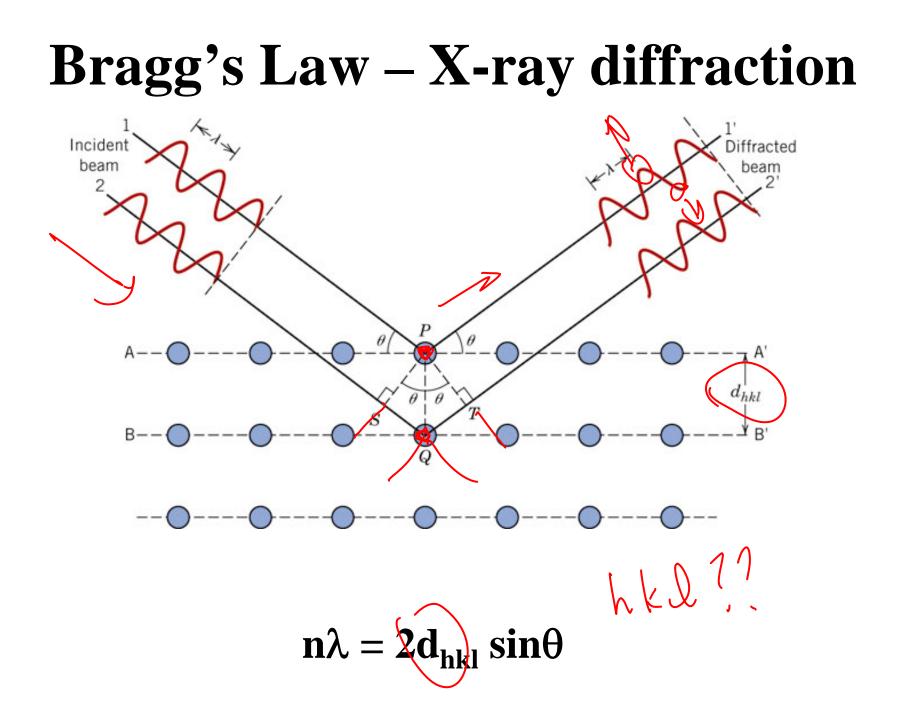
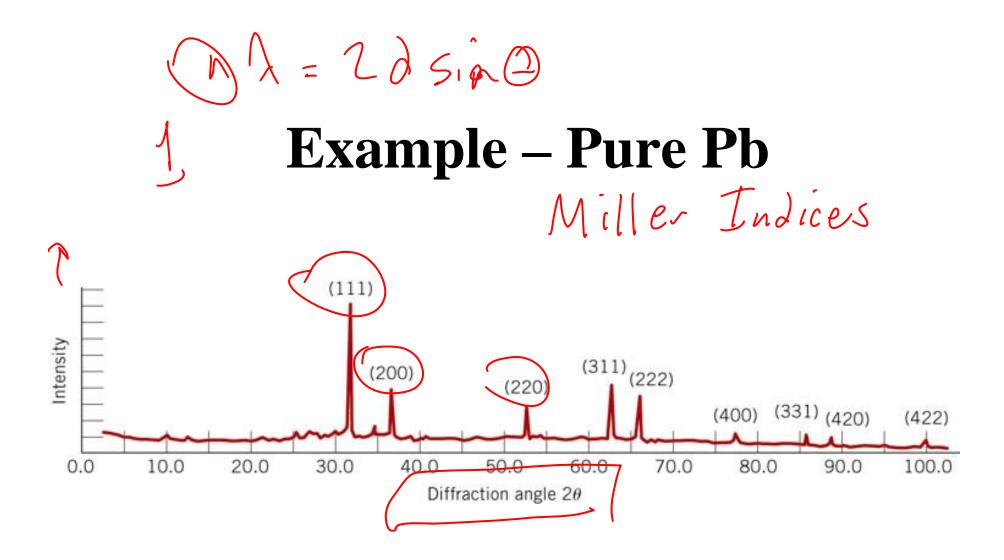


Figure 2 GaAs/GaP nanowire junctions. **a**, High-resolution TEM of a GaAs/GaP junction grown from a 20-nm gold nanocluster catalyst. Scale bar, 10 nm. Inset, two-dimensional Fourier transforms of the entire image show a splitting of the reciprocal lattice peaks along the $\langle 111 \rangle$, $\langle \bar{1}11 \rangle$ and $\langle \bar{2}00 \rangle$ lattice directions in the [$0\bar{2}2$] zone axis, corresponding to the lattice constants for GaAs and GaP (see text). The presence of the heterojunction was confirmed by EDS analysis above and below the junction region (not shown). **b**, TEM image of another junction. Scale bar, 20 nm. **c**, **d**, **e**, Elemental mapping of the Ga (shown

grey), P (red) and As (blue) content of the junction shown in **b**. A scanning TEM was used to take an elemental 'image' of the junction. **f**, Line profiles of the composition through the junction region, showing the change in composition as a function of the distance. The slightly higher Ga (shown black) signal relative to the P (red) and As (blue) signals may be due to uncertainties in the detector calibration or the presence of an amorphous gallium oxide layer around the crystalline nanowire core.





Callister has example of how this type of experiment is conducted.

Crystallographic Databases

65 3435			\frown				Wavelen	gth	1.7	88	97
AuSn		20	Int	h	k	I	2 θ	Int	Π		-
Gold Tin		27.646		1	0	0	115.192	11	1	0	5
		33.553		1	0	1	118.959	16	3	1	0
	N	37.799	23	0	0	2	122.456	19	3	1	1
		47.469	999*	1	0	2 🔰	125.440	5	2	2	2
Rad.: CuKa1 λ: 1.54060 Filter:	d-sp: Calculated	48.891	699	1	1	0	129.682	28	2	1	4
	a op. ouloulated	57.090	74	2	0	0	133.950	97	3	1	2
Cut off: Int.: Calculated	I/Icor.: 13.83	60.603	80	2	0	1	140.189	8	2	0	5
Ref: Calculated from NIST using PC		63.407	29	1	1	2	145.760	6	4	0	0
Ref: S.Stenbeck & A.Westgren, Z. P	nys. Chem. (B), B14, 91 (1931) 65.563	62	1	0	3	150.097	67	3	0	4
		70.520	279	2	0	2	152.692	4	0	0	6
		78.415	52	2	1	0	163.004	14	3	1	з
ys.: Hexagonal S.G.:	P6 ₃ /mmc (194)	80.756	45	0	0	4		42	1	0	6
. 4 000 h.	A: C: 1.2776	81.468	60	2	1	1		42	4	0	2
i: 4.323 b: 5.523	A: 0:1.2776	85.917	24	2	0	3		14	2	1	5
β : γ :	Z:2 mp:	87.337	36	1	0	4		11	3	2	0
af Ibid	·	90.516	244	2	1	2		62	2	2	4
Ref: Ibid.		91.577	89	з	0	0		39	3	2	1
\frown 1		94.587	1	З	0	1		8	1	1	6
		100.479	137	1	1	4		7	4	0	3
Dx: 11.728 Dm: ICSE	#:	103.731	7	3	0	2		22	3	1	4
		105.742	27	2	1	3		39	2	ò	6
		107.219		2	Ó	4		79	3	2	2
^p eak height intensity. As Ni type. PS /olume[CD]: 89.39.	C: hP4. Mwt: 315.66.	111.717		2	2	0		60	4	1	ō

20 Int h k i 1 4 1 1 ICDD[•] © 2001 JCPDS-International Centre for Diffraction Data. All rights reserved PCPDFWIN v. 2.2

Crystallographic Databases Pearson's

$Au_{-}Sn$

Phase diagram: Partial c-T diagram given for the concentration range 12-22 at.% Sn Reference: K. Osada, S. Yamaguchi and M. Hirabayashi, "An Ordered Structure of Aus Sn." TRANSACTIONS OF THE JAPAN INSTITUTE OF METALS, 15, 256-260 (1974)

AuSi a= 0.4322	1 2 nm		Structure AsNi = 0.55222 nm	Type Pear	son Symbol hP4	Space Group $P6_3/mmc$ $\gamma = 120^{\circ}$	No. 194	Hexagon
Au	2a	$\overline{3}m.$	x=0	y=0	z=0	occ. = 1	\checkmark	- uj
Sn	2c	<u>6</u> m2	x = 1/3	y = 2/3	z = 1/4	occ. = 1	C	
Diffractio	n data: Powder	Debye-Scherrer, C	u				-16-	
Preparatio	on: Starting con	nponents are Au an	d Sn (5N); melted	l in evacuated a	silica tube			Dasis
Reference	: J.S. Charlton,	M. Cordey-Hayes	and I.R. Harris, "	A STUDY OF	THE 119Sn M	IOSSBAUER IS	SOMER	
SHIFTS	IN SOME PL.	ATINUM-TIN AN	D GOLD-TIN A	LLOYS." JO	URNAL OF 2	THE LESS-CO	MMON	14000
METALS.	20, 105-112 (1	970)					4	inc/p

AuSr	1		Structure AsNi		Pearson Symbol hP4	Space Group P63/mmc	No. Qr e 194 +/	
a= 0.43218	8 nm		c = 0.55230 nm			$\gamma = 120$ °	the	
Au	2a	<u>3</u> m.	x=0	y = 0	z=0	occ. = 1	A.	ン
Sn	2c	$\overline{6}m2$	x = 1/3	y = 2/3	z=1/4	occ.=1	atoms "	(
Men allows	11 70	3 - 1 3					0,00	•

Miscellaneous: $d_m = 11.72 \text{ g/cm}^3$

Diffraction data: Powder, Guinier, Cu, R = 0.105

Preparation: Heated in evacuated silica tube; annealed at 563 K; guenched

T-, p- or concen.dependence: Au_xSn, x= 0.98-1.00, a= 0.43136-0.43218 nm, c= 0.55172-0.55230 nm, linear dependence

Reference: J.-P. Jan, W.B. Pearson, A. Kjekshus and S.B. Woods, "ON THE STRUCTURAL, THERMAL, ELECTRICAL. AND MAGNETIC PROPERTIES OF AuSn." CANADIAN JOURNAL OF PHYSICS, 41, 2252-2266 (1963)

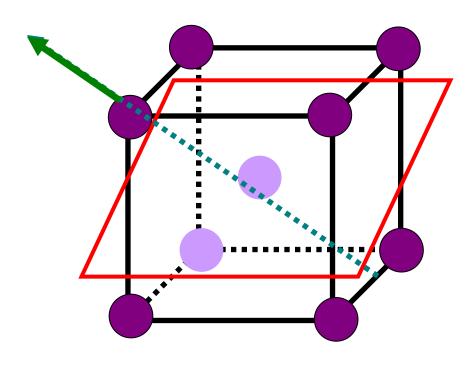
Summary (of pep talk)

- All of the crystal systems and their symmetry are 'known':
 - http://cst-www.nrl.navy.mil/lattice/
- If a new material comes up, a crystallographer can match the diffraction data to known systems and determine which is most likely and the atomic positions.
- If it is a known material, you can use XRD, ED to identify materials present and analyze its structure
 - Grain size, defects, stress 🥌
- For an electrical engineer, you would need to know how this all works.
 - You might be asked to characterize a material as part of your job
 - Or, you might need to communicate with another engineer that is characterizing your device for you.

CRYSTALLOGRAPHIC PLANES AND DIRECTIONS

Plane: plane section through a crystal or unit cell;

Direction: vector drawn through a crystal or unit cell



-different planes and directions have different atomic arrangements.

-therefore when crystals are subjected to external stimuli

(e.g. applied load, corrosive environment, magnetic props)

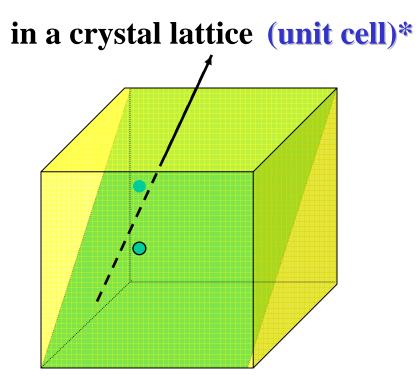
different planes and directions respond in different ways.

i.e. Property depends on crystal orientation

MILLER INDICES

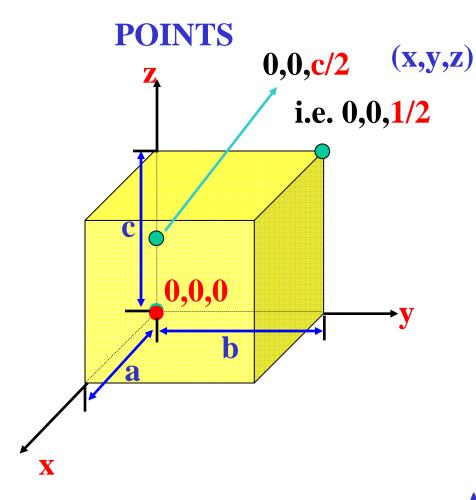
Notation used to describe specific

Jocations (points), directions, and planes



'representation'

CUBIC: simplest concept same for all unit cell types



Define coordinate system

right hand cartesian

Orient coordinate system align axes: parallel to unit cell edges

label axes (x,y,z)

define origin

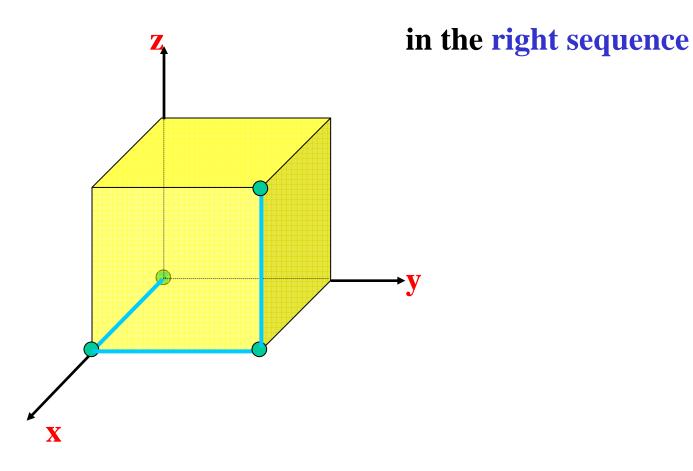
"arbitrary"

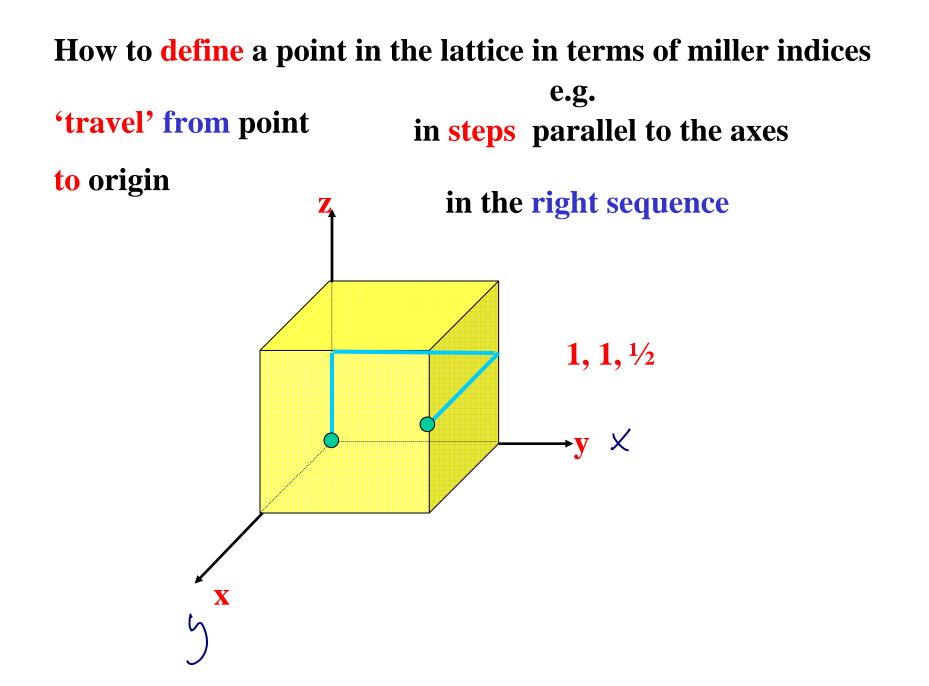
Always*: Define origin Label axes

Positions quantified as fractions of lattice parameters

How to locate a miller indices point in the lattice e.g. 1,1,1

'travel' from origin in **steps** parallel to the axes



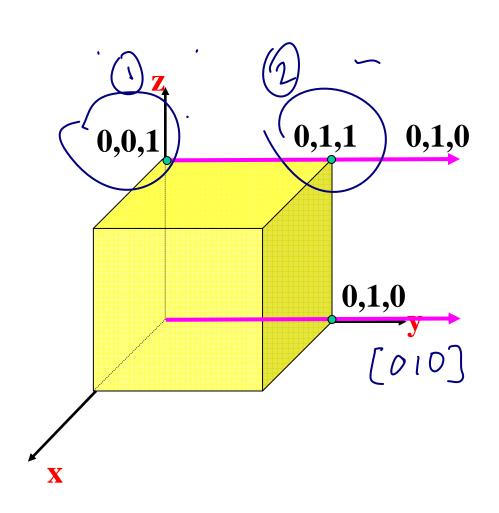


DIRECTIONS

How to define a given direction in terms of miller indices e.g.

determine coords of 2 points lying on the direction Subtract coords of '1st' point from the '2nd'

(As the crow flies)



Write indices in square brackets without commas [010] <--

Note: parallel directions have the same miller indices

(same direction!)

MOVE ORIGIN!

DIRECTIONS

How to **define** a **given direction** in terms of miller indices e.g.

determine coords of 2 points lying on the direction Subtract coords of '1st' point from the '2nd'

(As the crow flies)

0,1,0 0,1,0 0,0,0

Write indices in square brackets without commas [010]

Note: parallel directions have the same miller indices

(same direction!)

MOVE ORIGIN!

DIRECTIONS

Directions are integers

eliminate fractions by

multiplying by one factor....

to obtain lowest possible miller indices (integer)

In this case, multiply by.....

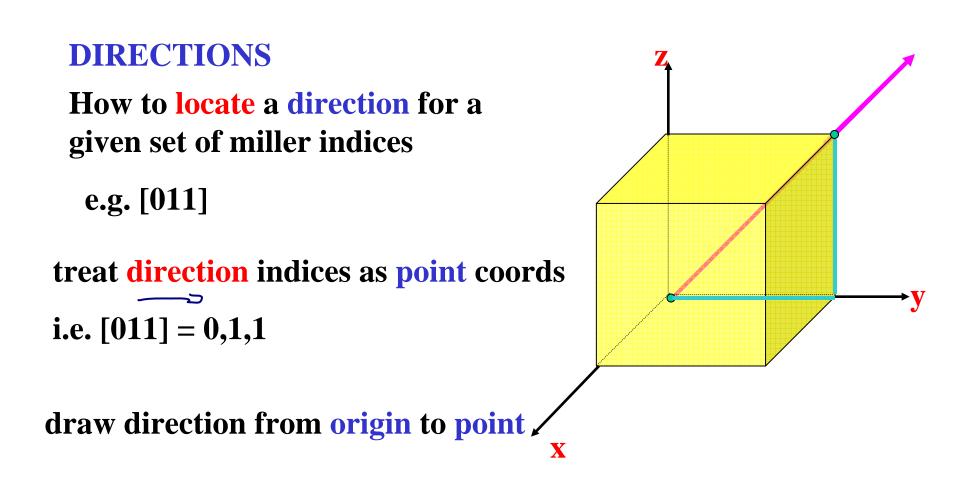
[0 1 0]

x Subtract coords of '1st' point from the '2nd' (As the crow flies)

0,1/2,1

0,0,1

 $0, \frac{1}{2}$



Note

Directions for given miller indices always originate from the origin

NEGATIVE DIRECTIONS For a given (negative) direction

e.g.

determine coords of 2 points lying on the direction Subtract coords of 1st point from the 2nd (as the crow flies)

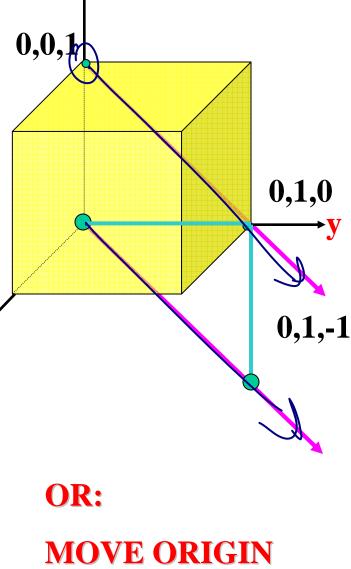
Write indices in square brackets without commas [011]

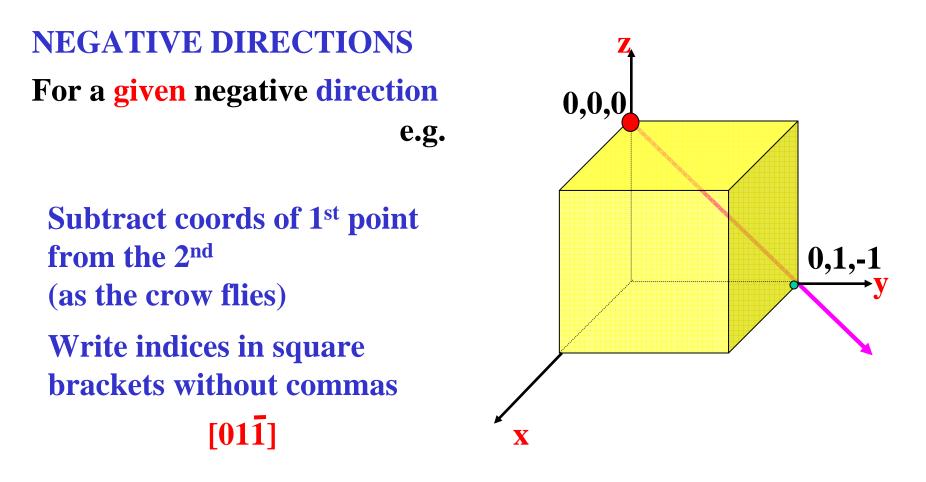
for given 'negative' miller indices

e.g. [011]

treat the indices as coords of a point

0,1,-1



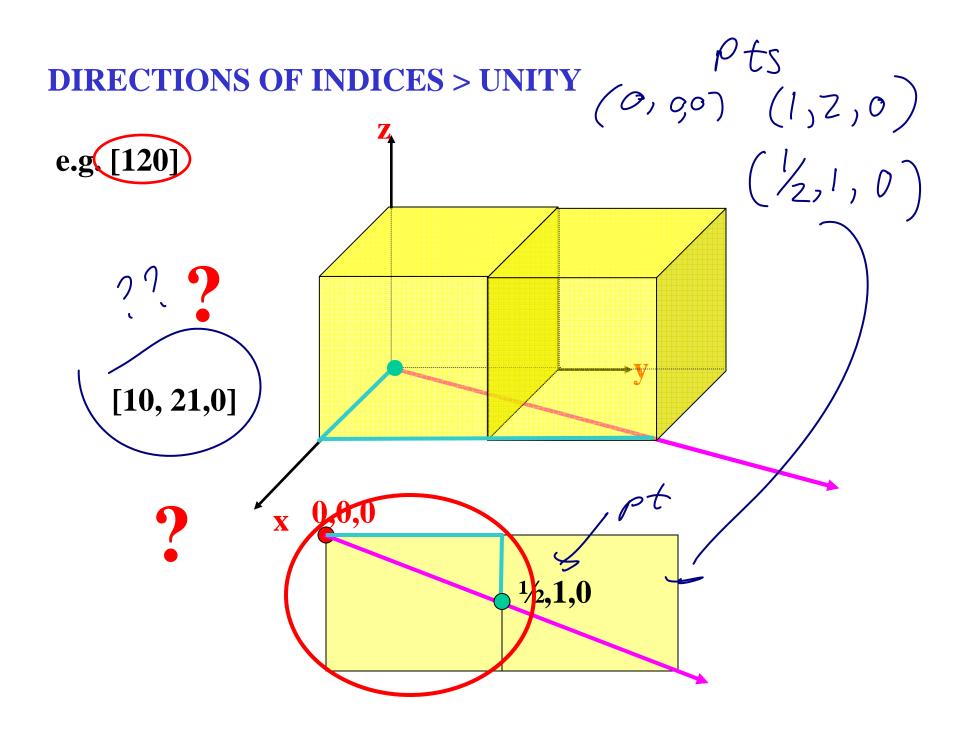


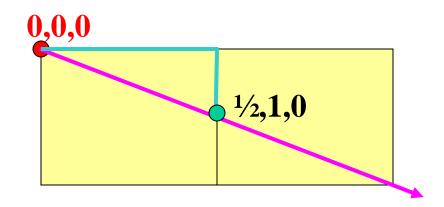
for given 'negative' miller indices

e.g. [011] 0,1,-1

OR: MOVE ORIGIN

treat the indices as coords of a point





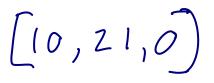
[120] is converted to ¹/₂,1,0 ?

by dividing throughout by 2

To draw direction of miller indices > 1

Using only one cell

convert miller indices to coords (fractional coords)

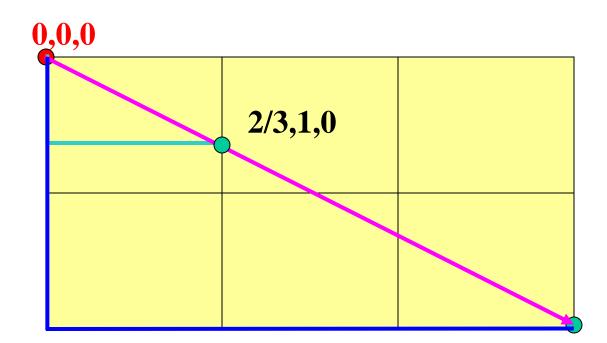


i.e. by dividing by the highest miller index

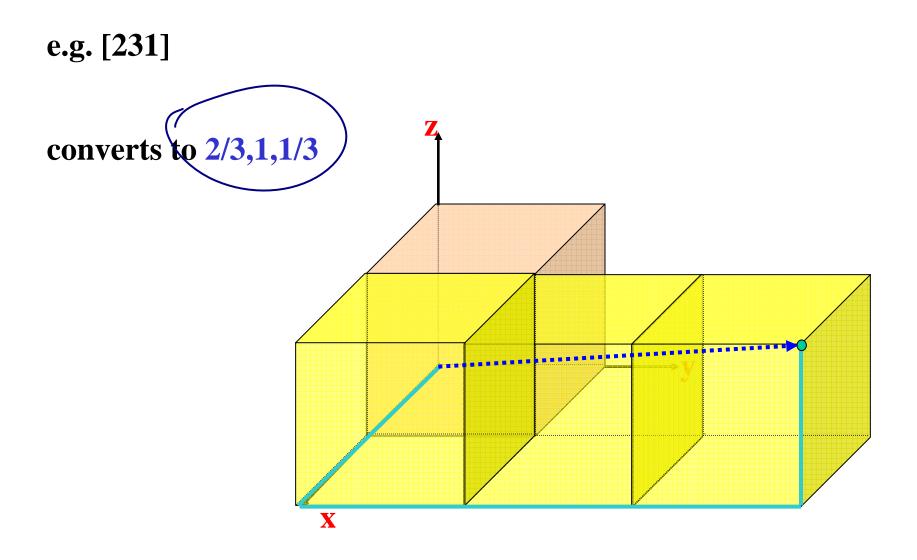
DIRECTIONS OF INDICES > UNITY

e.g. [230]

converts to 2/3,1,0

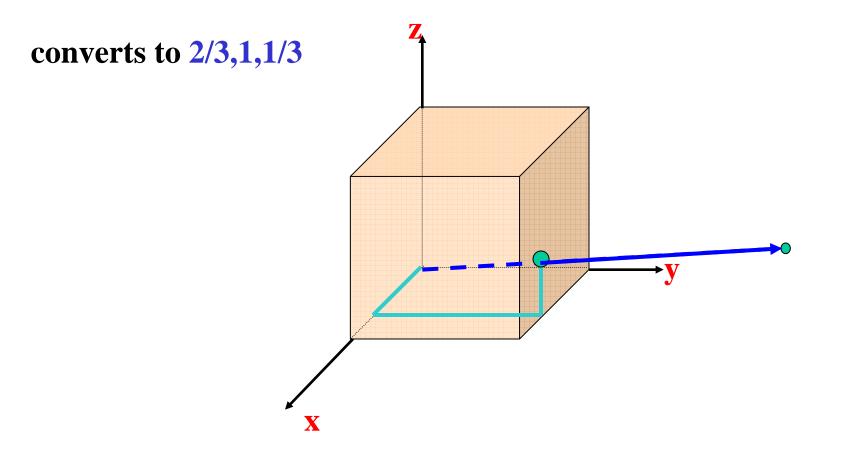


DIRECTIONS OF INDICES > UNITY



DIRECTIONS OF INDICES > UNITY

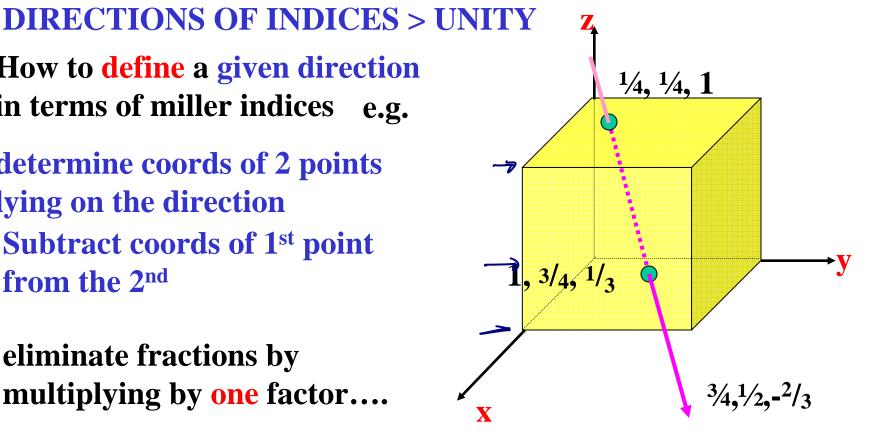
e.g. [231]



How to define a given direction in terms of miller indices e.g.

determine coords of 2 points lying on the direction Subtract coords of 1st point from the 2nd

eliminate fractions by multiplying by one factor....



to obtain lowest possible miller indices use (4*3)

9,6,-8

Write indices in square brackets without commas

[96]

Questions?

PLANES

How to **define** a **given plane** in terms of miller indices, e.g.

determine the points at which the plane intersects the 3 axes

take reciprocal of points

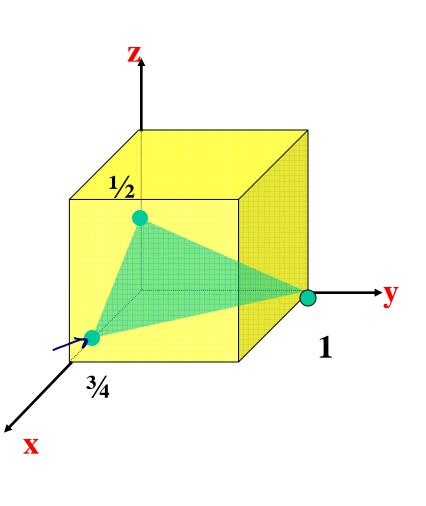
⁴/₃, 1, 2

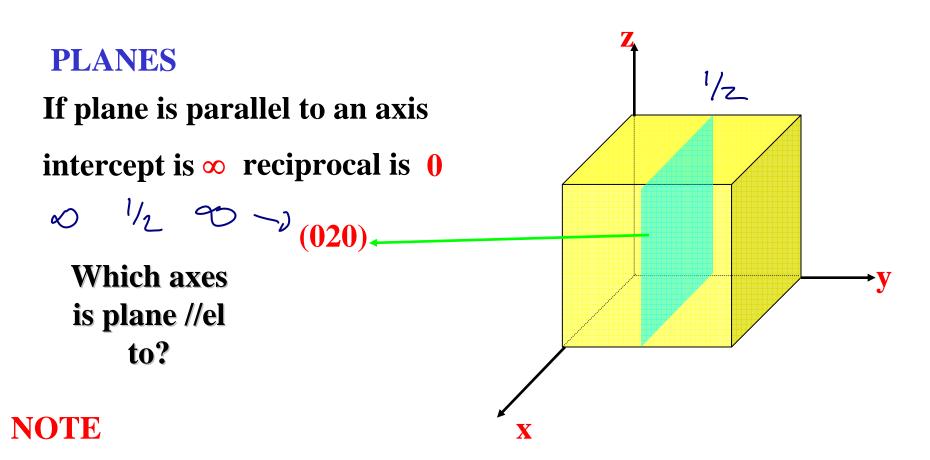
clear fractions by multiplying throughout by **3**

436

(clear commas)

DON'T reduce to lowest integers correct Miller Indices add parentheses (436)

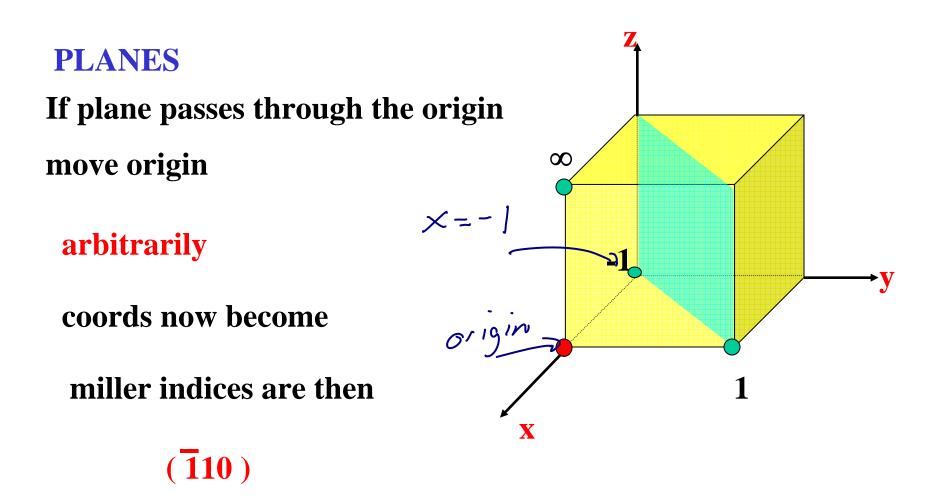


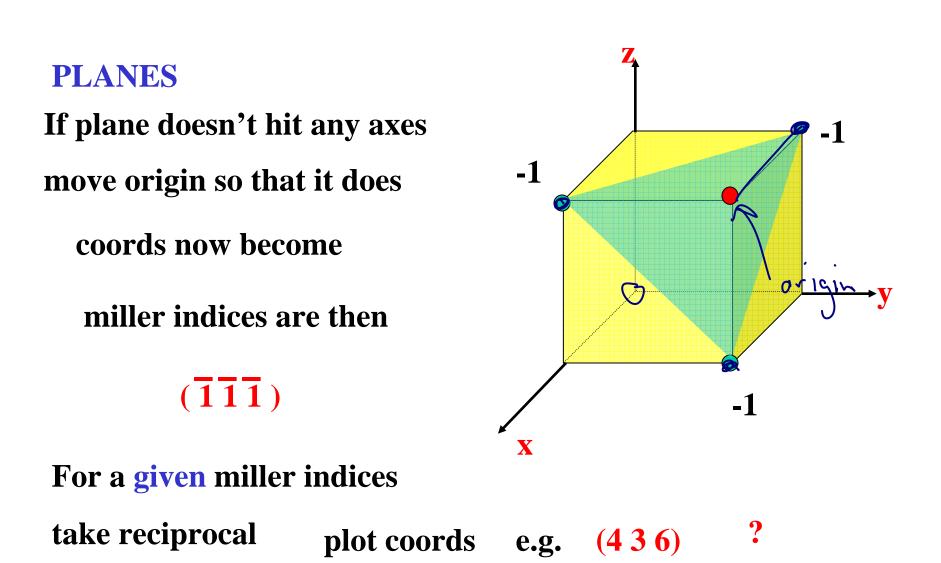


miller indices of **PLANES** are integers with ratios

the same as the ratios of the reciprocals of the intercepts

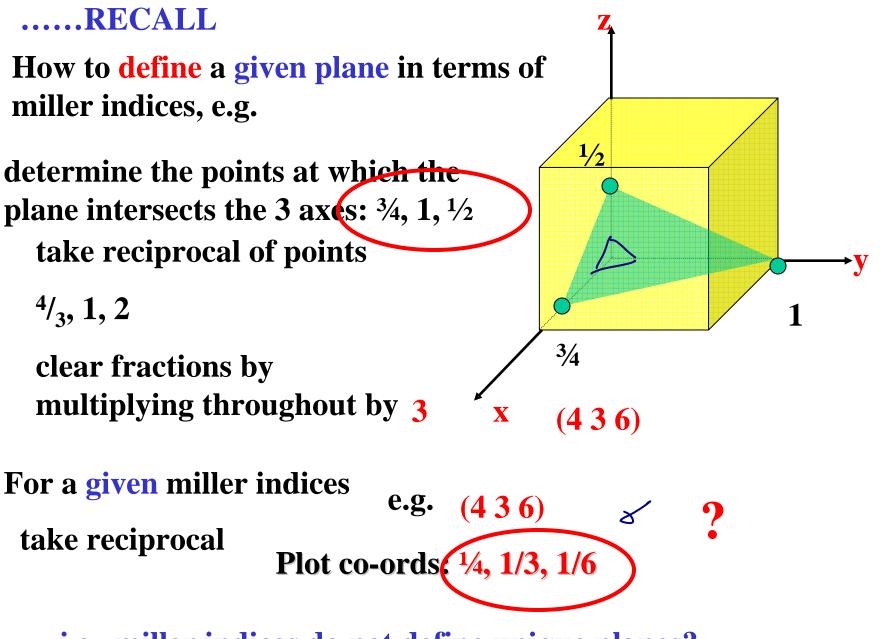
any fractions are cleared by multiplying throughout by one factor





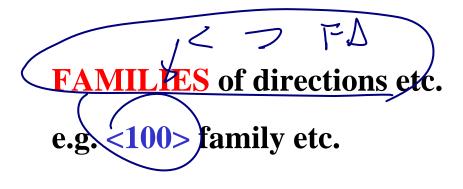
Plot co-ords: 1/4, 1/3, 1/6

BUT....



i.e. miller indices do not define unique planes?

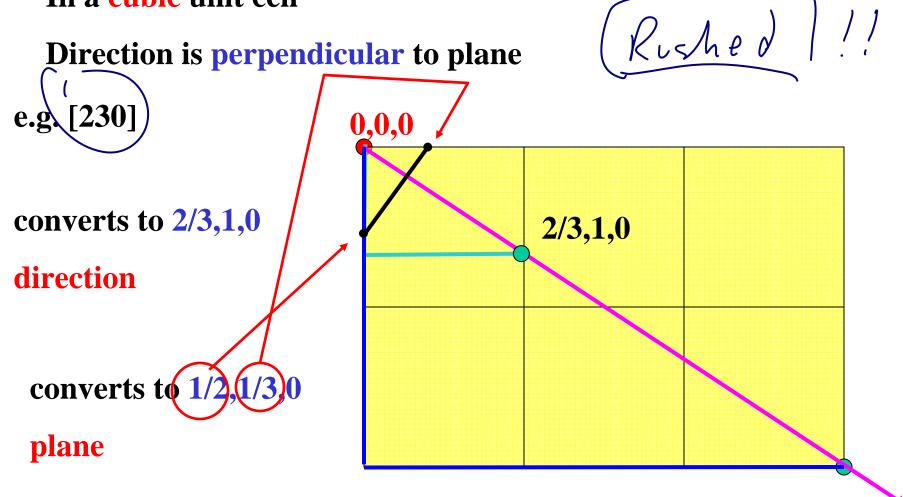
FAMILY FAMILIES of planes have the same atomic configuration e.g. {100} family consists of all combinations of these indices including negatives

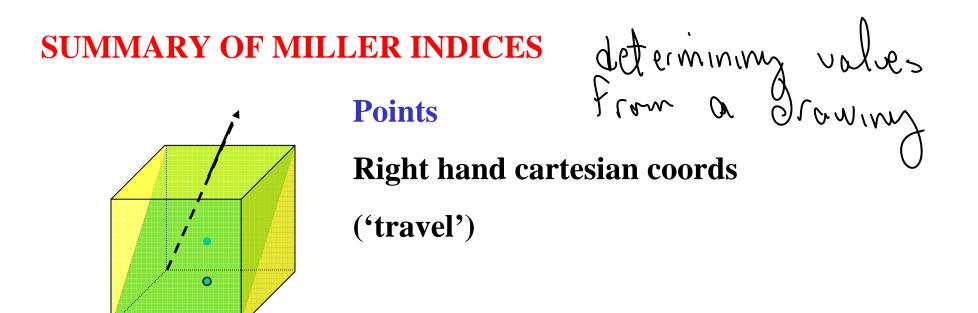


for a cubic cell

ALSO Relationship between planes and directions

In a cubic unit cell





Directions Define 2 co-ords; Subtract first one from second one Clear fractions; [u v w]

PlanesDefine intercepts on the three axesTake reciprocalsClear fractions;(h k l)

0-spacing

SUMMARY OF MILLER INDICES

From given indices:

making a drawing from given values

Points

Right hand cartesian coords ('travel')

DirectionsDivide throughout by highest indexPlot corresponding pointconnect origin to point

Planes Take reciprocals

Plot intercepts on the three axes

-Crystallographic differences between planes and directions

quantified by linear and planar atomic density, (LAD and PAD)

-analogous to APF (atomic packing factor, which was 'volume atomic density')

 $Linear atomic density = \frac{length of line intersected by atoms}{total line length}$

Planar atomic density = $\frac{\text{Area of plane intersected by atoms}}{\text{total plane area}}$

Anisotropy

Table 3.3 Modulus of Elasticity Values for Several Metals at Various Crystallographic Orientations

	Modulus of Elasticity (GPa)					
Metal	[100]	[110]	[111]			
Aluminum	63.7	72.6	76.1			
Copper	66.7	130.3	191.1			
Iron	125.0	210.5	272.7 🧲			
Tungsten	384.6	384.6	384.6			

Source: R. W. Hertzberg, *Deformation and Fracture Mechanics of Engineering Materials*, 3rd edition. Copyright © 1989 by John Wiley & Sons, New York. Reprinted by permission of John Wiley & Sons, Inc.

SINGLE CRYSTALS AND POLYCRYSTALS -A group of one or more unit cells = a single crystal (a grain)

-A group of more than one grain = a polycrystal

(but not termed a polygrain!)

-Under normal (i.e. industrial) circumstances, all crystalline solids are polycrystals Liquids can be made to solidify as a single crystal (Single crystals are very important in the electronics and aerospace industries.)